

IN THE CLAIMS

Please amend the claims as follows:

1. (Currently Amended) A gas reaction apparatus comprising:
a vaporizer for producing a reaction gas by vaporizing a liquid source material; and
a reaction chamber in which the reaction gas reacts,
wherein the vaporizer is configured as a unit for constituent members forming the reaction chamber, and the reaction gas produced in the vaporizer is directly introduced into the reaction chamber,
wherein the vaporizer includes a spraying nozzle, a vaporizing chamber forming a spraying space of a corresponding spraying nozzle, a narrow passageway communicating with the corresponding vaporizing chamber, a draining unit communicating with the corresponding narrow passageway, and a source gas diffusion space communicating with the draining unit and the reaction chamber, and
wherein a valve body for opening or closing the draining port is disposed, and a filter for capturing solid or liquid phase materials in the reaction gas is disposed to surround the valve body.

2. (Original) The gas reaction apparatus of claim 1, wherein the vaporizer is directly formed at an outer side of a gas introduction unit for introducing the reaction gas into the reaction chamber.

3. (Original) The gas reaction apparatus of claim 1, wherein the vaporizer is formed above the reaction chamber.

4. (Canceled)

5. (Previously Presented) The gas reaction apparatus of claim 1, wherein the narrow passageway is formed of one or more passageways annularly disposed around the vaporizing chamber, and an annular draining passage communicating with the narrow passageway is disposed in the draining unit.

6. (Previously Presented) The gas reaction apparatus of claim 1, comprising a heater unit for heating inner surfaces of the vaporizing chamber and the narrow passageway.

7. (Currently Amended) The gas reaction apparatus of claim 5, wherein the filter for capturing solid or liquid phase materials in the reaction gas is disposed inside the draining passage.

8. (Original) The gas reaction apparatus of claim 7, wherein the filter is disposed at a draining port of the draining passage, which communicates with the reaction chamber.

9. (Canceled).

10. (Original) The gas reaction apparatus of claim 7, comprising a heater unit for heating the filter.

11. (Previously Presented) The gas reaction apparatus of claim 10, wherein the filter makes a thermal contact with an inner surface of the draining passage, and is heated by the heater through the inner surface of the draining passage.

12. (Original) The gas reaction apparatus of claim 11, wherein a heat transfer unit, thermally contacted with a portion other than edges of the filter, is disposed at the draining passage.

13. (Currently Amended) A semiconductor processing apparatus, comprising:
a vessel forming a processing chamber for processing a substrate to be processed, the vessel having a upper plate capable of being attached thereto and detached therefrom;
a supporting member, disposed inside the vessel, for supporting the substrate to be processed;
a showerhead for supplying a processing gas into the processing chamber, the showerhead being disposed below the upper plate to face the substrate supported by the supporting member;
a vaporizing chamber, disposed on the upper plate, for producing the processing gas by vaporizing a liquid source material;
a gas passage, configured to communicate with the vaporizing chamber, for flowing the processing gas; and
a draining unit for communicating with the gas passage through the upper plate, wherein the showerhead includes a source gas diffusion space communicating with the draining unit and the processing chamber, and
wherein a cap is installed on the upper plate and a valve for opening or closing the draining hole is installed at the cap.

14. (Currently Amended) The semiconductor processing apparatus of claim 13, wherein the vaporizing chamber is formed as a space between the upper plate and ~~[[a]]~~ the cap installed on the upper plate.

15. (Original) The semiconductor processing apparatus of claim 14, wherein the gas passage includes a narrow passageway formed by a fine gap of 0.5 ~ 10.0 mm between the cap and the upper plate, and the narrow passageway serves as a path for vaporizing a mist contained in the processing gas.

16. (Original) The semiconductor processing apparatus of claim 15, wherein a protrusion defining a sidewall of the vaporizing chamber is formed on the upper plate, and the narrow passageway is formed between a top surface of the protrusion and an inner surface of the cap.

17. (Original) The semiconductor processing apparatus of claim 16, wherein the gas passage includes an annular passageway formed to surround the vaporizing chamber between an outer surface of the protrusion and the inner surface of the cap, and a draining hole is formed at the upper plate towards the showerhead from the annular passageway.

18. (Canceled).

19. (Original) The semiconductor processing apparatus of claim 14, wherein there is further included a spraying nozzle, installed at the cap, for spraying the liquid source material into the vaporizing chamber.

20. (Original) The semiconductor processing apparatus of claim 14, wherein the upper plate is coupled to a main body of the vessel through a hinge, and the upper plate and the cap rotate as a unit around the hinge as a center with respect to the main body of the vessel.